IN THE CLAIMS:

Please amend the claims where indicated below:

1. (*currently amended*) A vertical cavity surface emitting laser, comprising:

an active region further comprising at least one quantum well having a depth of at least 40 meV, wherein said depth is defined ~~as~~using the difference between a valence band offset and a conduction band offset, said quantum well being comprised of InGaAs and further including GaAs barrier layers sandwiching said at least one quantum well; and

GaAs confinement layers sandwiching said active region.

2. (*previously submitted*) The vertical cavity surface emitting laser of claim 1 wherein said at least one quantum well is up to and including 50Å in thickness.

3. (*currently amended*) A vertical cavity surface emitting laser, comprising:

an active region further comprising at least one quantum well having a ~~well~~ depth of at least 40 meV, wherein said depth is defined ~~as~~using the difference between a valence band offset and a conduction band offset, said quantum well being comprised of InGaAs and further including GaAsN barrier layers sandwiching said at least one quantum well; and

AlGaAs confinement layers sandwiching said active region.

4. (*previously amended*) The vertical cavity surface emitting laser of claim 3 wherein said at least one quantum well is up to and including 50Å in thickness.

~~5. (currently amended) A vertical cavity surface emitting laser, comprising:~~

an active region further comprising at least one quantum well having a depth of at least 40 meV, wherein said depth is defined ~~as~~using the difference between a valence band offset and a conduction band offset, said quantum well being comprised of InGaAs and further including AlGaAs barrier layers sandwiching said at least one quantum well; and

GaAsN confinement layers sandwiching said active region.

6. (*previously amended*) The vertical cavity surface emitting laser of claim 5 wherein said at least one quantum well is up to and including 50Å in thickness.